

EAUT-10677350.wsp.1

File View Edit Tools Window Help

0 1 2 3 4 5 6 7 8 9 A B C D E F G H I J K L M N O P Q R S T U V W X Y Z [ \ ] ^ \_ ` a b c d e f g h i j k l m n o p q r s t u v w x y z { | } ~

(0) ((((((vertical adj3 transistor).ti.) not (((ver  
(21) (vertical adj transistor) and (monocrystalline a  
(91) (vertical adj transistor) and (plug with (dielec  
(70) ((vertical adj transistor) and (plug with (diel  
(5) (((vertical adj transistor) and (plug with (diel  
(65) (((vertical adj transistor) and (plug with (die  
(61) (((vertical adj transistor) and (plug with (di  
(49) (((vertical adj transistor) and (plug with (c  
(12) (((vertical adj transistor) and (plug with (c  
(642) (vertical adj transistor) and (trench with (die  
(574) ((vertical adj transistor) and (trench with (di  
(566) (((vertical adj transistor) and (trench with (c  
(125) (((vertical adj transistor) and (trench with (c  
(111) (((vertical adj transistor) and (trench with  
(103) (((vertical adj transistor) and (trench with  
(22) (((vertical adj transistor) and (trench with

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Default operator: OR

Highlight all hit terms initially

(((vertical adj transistor) and (plug with (dielectric or  
insulat\$4))) not ((vertical adj transistor) and (monocrystalline adj  
silicon) and (plug with (dielectric or insulat\$4))) and  
(monocrystalline)

US 6207977 20010327 63 Vertical MISFET devices 257/192 257/19;  
257/194;  
257/331;  
US 5963800 19991005 60 CMOS integration process having 438/212 257/334;  
257/E21.643;  
257/E27.062;  
US 5920088 19990706 61 Vertical MISFET devices 257/192 257/194;  
257/330;  
257/E21.643;  
US 5914504 19990622 60 DRAM applications using vertical 257/192 257/195;  
257/200;  
257/201;  
US 5010386 19910423 8 Insulator separated vertical CMOS 257/369 257/328;  
257/623;  
257/E27.062

	U	I	PT	P	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor	S	C
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6207977 B1	20010327	63	Vertical MISFET devices	257/192	257/19; 257/194; 257/331;	Augusto, Carlos Jorge Ramiro Proenca	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 5963800 A	19991005	60	CMOS integration process having vertical channel	438/212	257/334; 257/E21.643; 257/E27.062;	Augusto, Carlos Jorge Ramiro Proenca	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 5920088 A	19990706	61	Vertical MISFET devices	257/192	257/194; 257/330; 257/E21.643;	Augusto, Carlos Jorge Ramiro Proenca	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 5914504 A	19990622	60	DRAM applications using vertical MISFET devices	257/192	257/195; 257/200; 257/201;	Augusto, Carlos Jorge Ramiro Proenca	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 5010386 A	19910423	8	Insulator separated vertical CMOS	257/369	257/328; 257/623; 257/E27.062	Groover, III, Robert	<input type="checkbox"/>	<input type="checkbox"/>

Details HTML

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